

# GU-84b

## Tetrode

The GU-84B tetrode is used for power amplification in traveling-wave and single-sideband signal amplifier circuits and as power amplifiers in RF equipment up to 250MHz.

### GENERAL

Cathode: indirectly heated, oxide-coated.

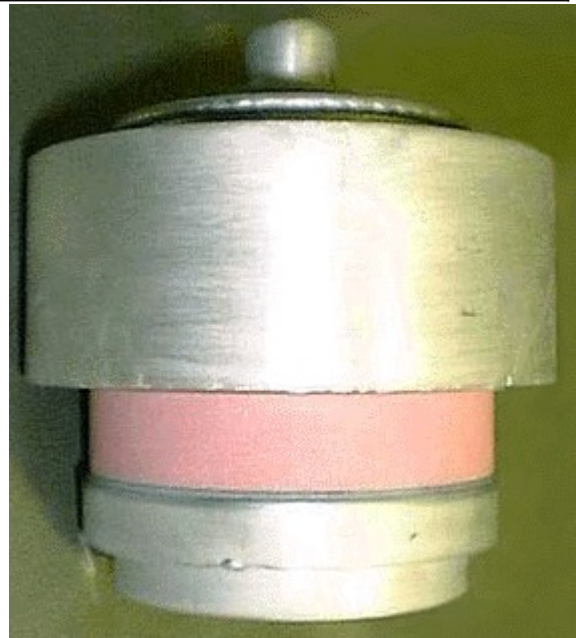
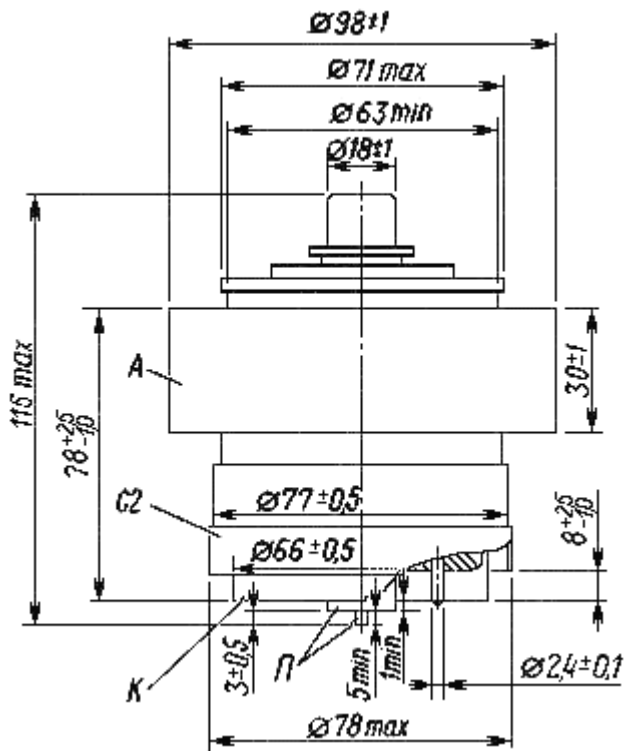
Envelope: metal ceramic.

Cooling: forced air - 96 m<sup>3</sup> / hr ( just under 57 CFM) at 30mm H<sub>2</sub>O for 1600W dissipation

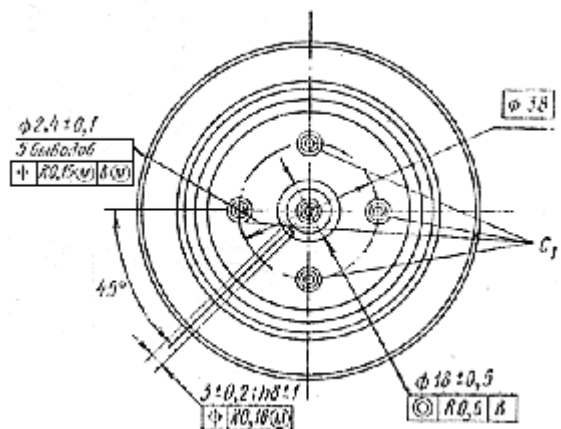
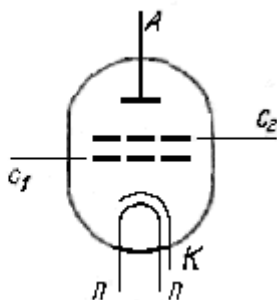
Height, mm, at most: 115

Diameter, mm, at most: 99

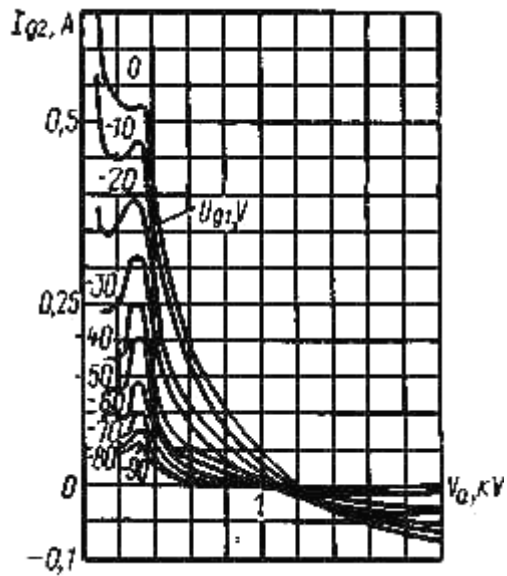
Mass, Kg, at most: 1.5



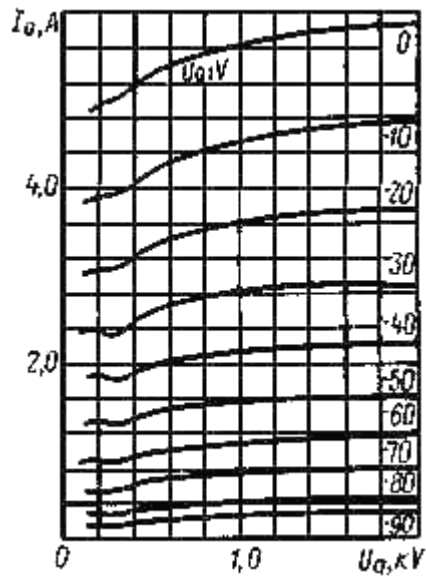
К — катод  
 П, П — подогреватель  
 С<sub>1</sub> — первая сетка  
 С<sub>2</sub> — вторая сетка  
 А — анод



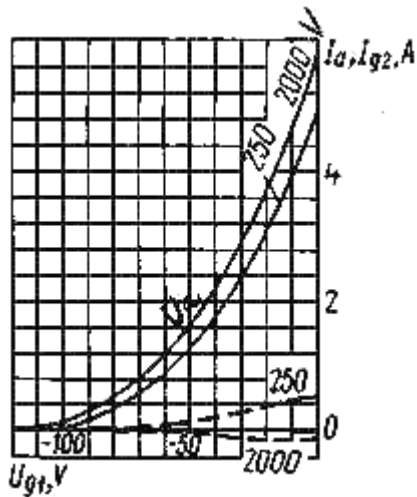
ENVIRONMENTAL OPERATING CONDITIONS	
Vibration loads:	
frequency, Hz	1-80
acceleration, m/s <sup>2</sup>	50
Multiple impacts with acceleration, m/s <sup>2</sup>	150
Ambient Conditions:	
Temperature, °C	-10 to +55
Relative humidity at up to +35 °C, %	98
NOMINAL ELECTRICAL PARAMETERS	
Heater voltage, V	27.0
Heater current, A	3.7
Mutual conductance ( $V_a = 750V$ , $V_{g2} = 375V$ , $I_a = 2A$ , change in $V_{g1} = 1V$ ), mA/V:	71
Negative bias ( $V_{g1}$ ) with $V_a = 750V$ , $V_{g2} = 375V$ , $I_a > 2A$ , V:	10-50
Negative cutoff bias ( $V_{g1}$ ) with $V_a = 2KV$ , $V_{g2} = 375V$ , $I_a = 20mA$ , V:	150
input capacitance, pF	102.5
output capacitance, at most, pF	20.5
transfer capacitance, pF	<0.2
Warm up time, s:	<180
AB <sub>1</sub> Output, $V_a = 2KV$ , $V_{g2} = 375V$ , $I_{g1} < 0mA$ , $I_{g2} > 80mA$ , frequency 0.1-1 MHz, KW:	>1.5
Designed Tube Life (hours)	>1500
ELECTRICAL PARAMETER LIMITS	
Heater voltage, V	25.6-28.4
Heater current, A	3.4-4.0
input capacitance, pF	90-115
output capacitance, pF	18-23
Maximum CW Anode voltage ( $V_a$ ), KV:	2.2
"Maximum" Control Grid voltage ( $V_{g1}$ ), V	-150
Maximum Screen Grid voltage ( $V_{g2}$ ), V	400
CW cathode current ( $I_c$ ), A:	2
Peak cathode current ( $I_c$ ), A:	6
Anode Dissipation, W:	2500
Screen Grid (G2) Dissipation, W:	30
Control Grid (G1) Dissipation, W:	1
Temperature at envelope (hottest point), °C	200
Frequency, MHz:	<250



Averaged Grid-Anode Characteristic Curves:  
 $U_f = 27V; U_{g2} = 400V$



Averaged Anode Characteristic Curves:  
 $U_f = 27V; U_{g2} = 400V$



Averaged Anode-Grid and Grid Characteristic Curves:  
 $U_f = 27V; U_{g2} = 400V;$   
 ———  $I_a;$   
 - - -  $I_{g2}$